



(51) International Patent Classification:
H01L 21/3213 (2006.01) *H10B 43/27* (2023.01)
H10B 41/27 (2023.01)

(21) International Application Number:
PCT/US2022/046318

(22) International Filing Date:
11 October 2022 (11.10.2022)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
17/689,092 08 March 2022 (08.03.2022) US

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(54) Title: METAL DEPOSITION AND ETCH IN HIGH ASPECT-RATIO FEATURES

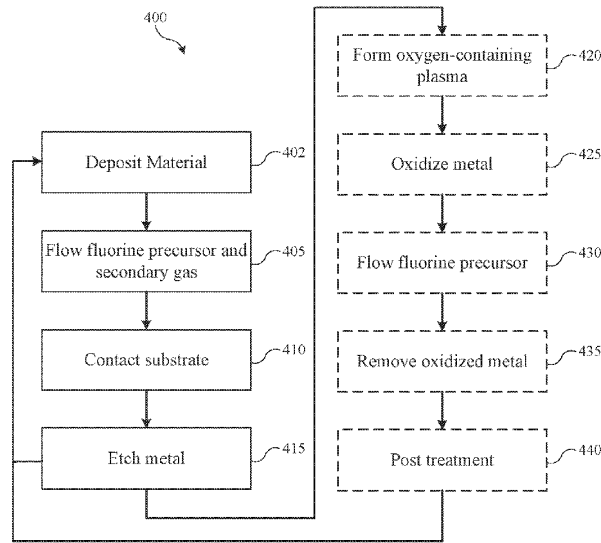


FIG. 4

(57) Abstract: Exemplary methods of etching may include flowing a fluorine-containing precursor and a secondary gas into a processing region of a semiconductor processing chamber. The secondary gas may be or include oxygen or nitrogen. A flow rate ratio of the fluorine-containing precursor to the secondary gas may be greater than or about 1:1. The methods may include contacting a substrate with the fluorine-containing precursor and the secondary gas. The substrate may include an exposed metal. The substrate may define a high aspect-ratio structure. The methods may include etching the exposed metal within the high aspect-ratio structure.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))